Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Rating		Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^{\circ}$ to 125°C)	BTB16-600BW3G BTB16-700BW3G BTB16-800BW3G	V _{drm} , V _{rrm}	600 700 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T_c = 8	0°C)	I _{T (RMS)}	16	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wa	I _{tsm}	170	А	
Circuit Fusing Consideration (t = 8.3 ms)		l²t	120	A ² sec
Non–Repetitive Surge Peak Off–State Voltage ($T_1 = 25^{\circ}$ C, t = 8.3 ms)		V_{DSM}/V_{RSM}	$V_{\text{DSM}}/V_{\text{RSM}}$ +100	V
Peak Gate Current (T _⊥ = 125°C, t ≤ 20µs)		I _{gM}	4.0	W
Average Gate Power ($T_{J} = 125^{\circ}C$)		P _{G(AV)}	1.0	W
Operating Junction Temperature Range		TJ	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

Recommended Operating Conditions may affect device reliability.
1. V_{DBM} and V_{RBM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance	Junction-to-Case (AC) Junction-to-Ambient	R _{øjc} R _{øja}	1.9 60	°C/W
Maximum Lead Temperature for Soldering Purpose	s, 1/8" from case for 10 seconds	T,	260	°C

Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I _{DRM} ,	-	-	0.005	
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I	-	-	2.0	mA

Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$)		V _{TM}	-	-	1.55	V
	MT2(+), G(+)		2.5	-	50	
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, \text{ R}_L = 30 \Omega$)	MT2(+), G(-)	I _{GT}	2.5	-	50	mA
	MT2(-), G(-)		2.5	-	50	
Holding Current ($V_D = 12$ V, Gate Open, Initiating Current = ±150 mA)		I _H	-	-	60	mA
	MT2(+), G(+)		-	-	70	
Latching Current ($V_p = 12 \text{ V}, I_g = 50 \text{ mA}$)	MT2(+), G(-)	I,	-	-	90	mA
	MT2(-), G(-)		-	-	70	
	MT2(+), G(+)		0.5	-	1.7	
Gate Trigger Voltage ($V_D = 12 \text{ V}, \text{ R}_1 = 30 \Omega$)	MT2(+), G(-)	V _{GT}	0.5	-	1.1	V
	MT2(-), G(-)		0.5	-	1.1	
	MT2(+), G(+)		0.2	-	-	
Gate Non-Trigger Voltage ($T_{J} = 125^{\circ}C$)	MT2(+), G(-)	V _{gd}	0.2	_	_	V
	MT2(-), G(-)		0.2	-	_	

Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.



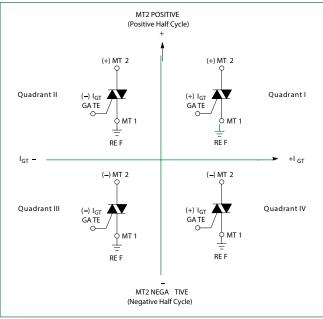
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Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T _J = 125°C, No Snubber)	(dl/dt)c	7.5	-	-	A/ms
Critical Rate of Rise of On–State Current (T _J = 125°C, f = 120 Hz, I _G = 2 x I _{GT} , tr \leq 100 ns)	dl/dt	-	-	50	A/µs
Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^{\circ}$ C)	dV/dt	1500	-	-	V/µs

Voltage Current Characteristic of SCR

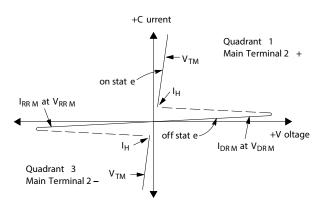
Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac

All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used





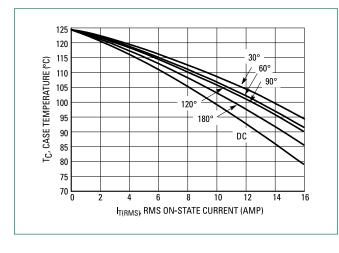


Figure 1. Typical RMS Current Derating

Figure 3. On–State Characteristics

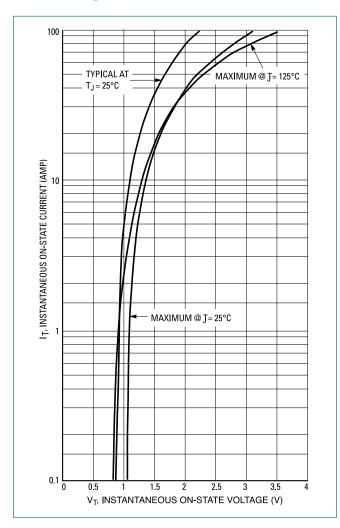


Figure 2. On-State Power Dissipation

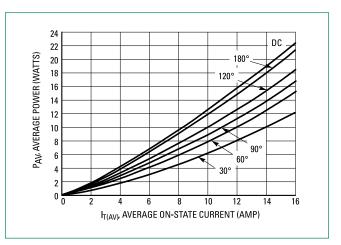
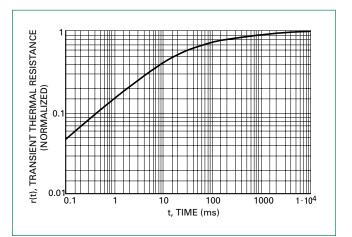
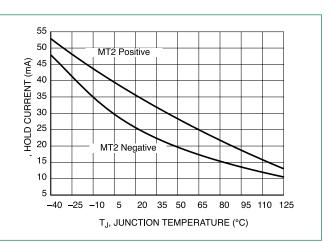


Figure 4. Thermal Response







Littelfuse

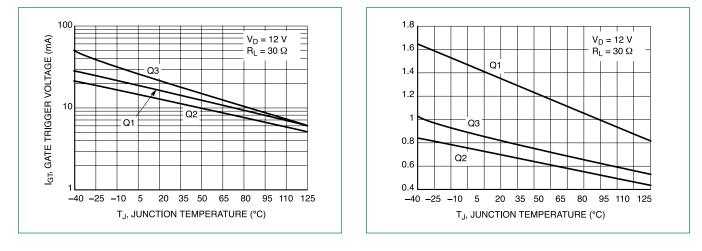
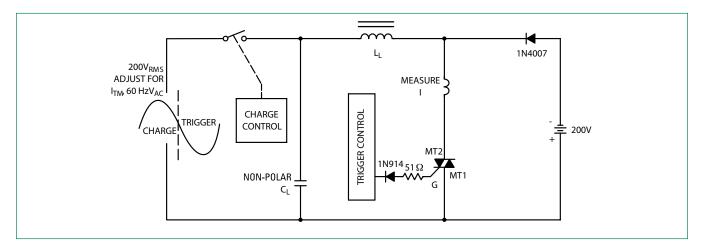


Figure 6. Typical Gate Trigger Current Variation

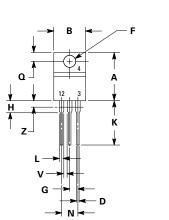
Figure 7. Typical Gate Trigger Voltage Variation

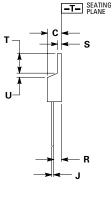
Figure 8. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



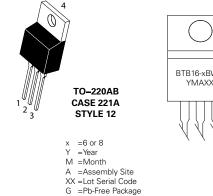
Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information

Dimensions





Part Marking System



	\bigcirc
	BTB16-xBWG YMAXX
l	

D:	Inc	hes	Millin	neters
Dim	Min	Мах	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
К	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
Ν	0.195	0.205	4.95	5.21
٥	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	-	1.15	-
Z	_	0.080	-	2.04

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

Ordering Information

Device	Package	Shipping
BTB16-600BW3G	TO-220AB (Pb-Free)	1000 Units / Box
BTB16-700BW3G	TO-220AB (Pb-Free)	1000 Units / Box
BTB16-800BW3G	TO-220AB (Pb-Free)	1000 Units / Box

1. Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

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